

## REVISIONS

Letter	ECO No.	Description	Checked	Approved	Date
A	36-109	INITIAL RELEASE	GG	EAB	10/20/94
B	36-140	ADD VENDOR NAME, PINOUTS, AND PACKAGE OUTLINE	G.G.	EAB	3-9-95

<b>NAME</b>	<b>DATE</b>	MASSACHUSETTS INSTITUTE OF TECHNOLOGY CENTER FOR SPACE RESEARCH			
Drawn: BRIAN KLATT	9/30/94	<b>MICROCIRCUIT, LINEAR, OPERATIONAL AMPLIFIER, TRANSCONDUCTANCE, MONOLITHIC, SILICON</b>			
Checked: G. GONG	10/20/94				
Approved: ED BOUGHAN	10/20/94				
Released: K. TIBBETTS	10/20/94				
		<b>Size</b>	<b>Code Identification No.</b>	<b>Drawing No.</b>	<b>Rev.</b>
		T	80230	36-02305	B
		Scale: NONE		Sheet: 1 of 10	

## 1.0 SCOPE

- 1.1 Introduction This drawing describes device requirements for an Operational Transconductance Amplifier (OTA) used in flight hardware for a space experiment on the AXAF CCD Imaging Spectrometer (ACIS) Instrument. The part described herein is a Harris Semiconductor die, part type CA3080A, packaged in a ten (10) lead ceramic flat pack.
- 1.2 Part Number The complete MIT part number shall be 36-02305
- 1.3 Absolute maximum ratings Absolute maximum ratings are in accordance with page 2-74 of Harris 1993-1994 Data Book DB500B.
- 1.4 Recommended operating conditions Recommended operating conditions are in accordance with page 2-74 of Harris 1993-1994 Data Book DB500B.

## 2.0 APPLICABLE DRAWINGS

- 2.1 Government Specifications and Standards Unless otherwise specified, the following specifications and standards, of the latest released issue, form a part of this drawing, to the extent specified herein.

### SPECIFICATIONS

#### MILITARY

MIL-M-38510                      Microcircuits, General Specification for

#### STANDARDS

MIL-STD-883                      Test Methods and Procedures for Microelectronics

#### INDUSTRY

Harris Semiconductor              1993-1994 Data Book DB500B

NOTE: Pages 2-73 through 2-76 of Harris Semiconductor 1993-1994 Data Book DB500B are included herein for convenience.

- 2.2 Order of precedence In the event of conflict between the text of this drawing and the references cited herein, the text of this drawing shall govern.

## 3.0 REQUIREMENTS

### 3.1 General Requirements

- 3.1.1 Item Requirements The microcircuits described herein shall, in all respects, meet all the requirements of this specification and the intent of MIL-M-38510 for a class B microcircuit. These microcircuits shall be fabricated and tested using production and test facilities and a Reliability and Quality Assurance program adequate to assure successful compliance with this specification and the intent of MIL-M-38510, as modified herein.

- 3.1.2 **Procuring Activity** For the purposes of this specification and documents referenced herein, the procuring activity is the Massachusetts Institute of Technology (MIT), Center for Space Research (CSR).
- 3.1.3 **Product Changes** The supplier shall notify MIT of proposed changes to Microcircuits, including changes in design, materials, fabrication methods, or processes, and changes which may affect the quality or intended end use.
- 3.2 **Part marking** Microcircuit marking shall meet the intent of paragraph 3.6 of MIL-M-38510.
- 3.2.1 **Part Identification Number (PIN)** Microcircuits shall be marked with the MIT part number; 36-02305.
- 3.3 **Electrical performance characteristics** Unless otherwise specified, the electrical performance characteristics are as specified in Harris Semiconductor 1993-1994 Data Book DB500B, electrical specifications for CA3080A, pages 2-75 and 2-76, and apply over the full operating temperature range.
- 3.4 **Design and Construction Requirements**
- 3.4.1 **Package** The package shall be a ten (10) lead, hermetically sealed, ceramic flat pack. See figure 1 herein. Leads shall be formed, after final electrical test, for surface mounting on a printed circuit board. Device hermeticity shall be tested after lead forming.
- 3.4.2. **Lead Finish** The lead finish shall be "A" per MIL-H-38510.
- 3.4.3 **Terminal connections** The terminal connections shall be the same as that for a dual in line package per Harris Semiconductor 1993-1994 Data Book DB500B, page 2-73. Also see table 1 herein.
- 4.0 QUALITY ASSURANCE PROVISIONS**
- 4.1 **Responsibility for Inspection** Unless otherwise specified herein, the supplier is responsible for the performance of all examinations and tests as specified herein.
- 4.2 **Screening** All Microcircuits (100%) shall be subjected to and pass the screen tests and examinations defined in paragraph 4.6 of MIL-M-38510, for a class B device.
- 4.2.1 **Xray** All Microcircuits (100%) shall be subjected to and pass radiographic examination per MIL-STD-883, method 2012.
- 4.2.2 **Particle Impact Noise Detection (PIND)** All Microcircuits (100%) shall be subjected to and pass PIND examination per MIL-STD-883, method 2020, condition B.
- 4.3 **Quality Conformance Inspection (QCI)** Quality conformance inspection shall be in accordance with paragraph 4.5 of MIL-M-38510, for a class B device.
- 4.4 **Destructive Physical Analysis (DPA)** An internal destructive examination shall be performed in accordance with paragraph 3.5, of MIL-STD-883, method 5009. Sample size shall be two (2) for lot sizes greater than 200, and one (1) sample for lot sizes of 200 or less.



# CA3080

## Operational Transconductance Amplifier (OTA)

April 1993

### Features

- Slew Rate (Unity Gain, Compensated).....50V/ms
- Adjustable Power Consumption.....10 $\mu$ W to 30 $\mu$ W
- Flexible Supply Voltage Range .....  $\pm 2V$  to  $\pm 15V$
- Fully Adjustable Gain ..... 0 to gm<sub>R<sub>L</sub></sub> Limit
- Tight g<sub>M</sub> Spread:
  - CA3080 ..... 2:1
  - CA3080A ..... 1.6:1
- Extended g<sub>M</sub> Linearity ..... 3 Decades

### Applications

- Sample and Hold
- Multiplexer
- Voltage Follower
- Multiplier
- Comparator

### Ordering Information

PART NUMBER	TEMP. RANGE	PACKAGE
CA3080	0°C to +70°C	8 Pin Can
CA3080A	-55°C to +125°C	8 Pin Can
CA3080AE	-55°C to +125°C	8 Lead Plastic DIP
CA3080AM	-55°C to +125°C	8 Lead SOIC
CA3080AM96	-55°C to +125°C	8 Lead SOIC*
CA3080E	0°C to +70°C	8 Pin Can
CA3080M	0°C to +70°C	8 Lead SOIC
CA3080M96	0°C to +70°C	8 Lead SOIC*

\* Denotes Tape and Reel

### Description

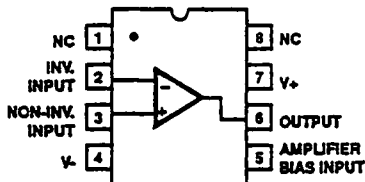
The CA3080 and CA3080A types are Gatable-Gain Blocks which utilize the unique operational-transconductance-amplifier (OTA) concept described in Application Note ICAN-6668, "Applications of the CA3080 and CA3080A High-Performance Operational Transconductance Amplifiers".

The CA3080 and CA3080A types have differential input and a single-ended, push-pull, class A output. In addition, these types have an amplifier bias input which may be used either for gating or for linear gain control. These types also have a high output impedance and their transconductance (g<sub>M</sub>) is directly proportional to the amplifier bias current (I<sub>ABC</sub>).

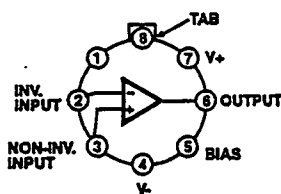
The CA3080 and CA3080A types are notable for their excellent slew rate (50V/ $\mu$ s), which makes them especially useful for multiplexer and fast unity-gain voltage followers. These types are especially applicable for multiplexer applications because power is consumed only when the devices are in the "ON" channel state.

The CA3080A is rated for operation over the full military-temperature range (-55°C to +125°C) and its characteristics are specifically controlled for applications such as sample-and-hold, gain-control, multiplex, etc. Operational transconductance amplifiers are also useful in programmable power-switch applications, e.g., as described in Application Note AN6048, "Some Applications of a Programmable Power Switch/Amplifier" (CA3094, CA3094A, CA3094B).

### Pinouts CA3080 (PDIP, SOIC) TOP VIEW

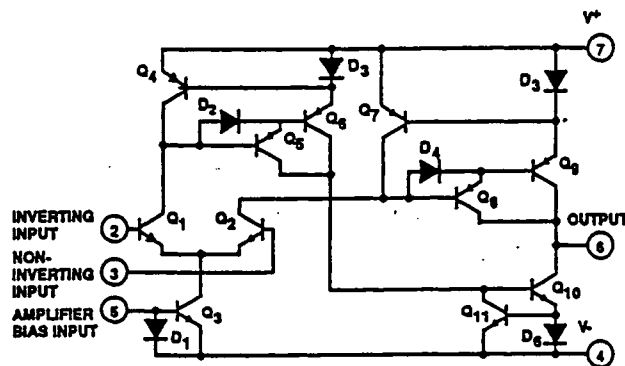


### CA3080 (TO-5 CAN) TOP VIEW



NOTE: Pin 4 is connected to case.

### Schematic Diagram



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper I.C. Handling Procedures.  
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File Number 475.2

**Specifications CA3080, CA3080A**

**Absolute Maximum Ratings**

Supply Voltage (Between V+ and V- Terminal).....	36V
Differential Input Voltage.....	5V
Input Voltage.....	V+ to V-
Input Signal Current.....	1mA
Amplifier Bias Current (I <sub>ABC</sub> ).....	.2mA
Power Dissipation.....	125mW
Output Short Circuit Duration (Note 1).....	No Limitation
Junction Temperature.....	+175°C
Junction Temperature (Plastic Package).....	+150°C
Lead Temperature (Soldering 10 Sec.).....	+300°C

**Operating Conditions**

Operating Temperature Range	CA3080..... 0°C to +70°C
	CA3080A..... -55°C to +125°C
Storage Temperature Range.....	-65°C to +150°C

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

**Electrical Specifications** For Equipment Design, T<sub>A</sub> = +25°C, Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS	CA3080 LIMITS			UNITS
		V+ = 15V, V- = -15V I <sub>ABC</sub> = 500µA	MIN	TYP	MAX	
Input Offset Voltage	V <sub>IO</sub>		-	0.4	5	mV
		T <sub>A</sub> = 0 to +70°C	-	-	6	mV
Input Offset Current	I <sub>IO</sub>		-	0.12	0.6	µA
Input Bias Current	I <sub>I</sub>		-	2	5	µA
		T <sub>A</sub> = 0 to +70°C	-	-	7	µA
Forward Transconductance (Large Signal)	g <sub>M</sub>		6700	9600	13000	µmho
		T <sub>A</sub> = 0 to +70°C	5400	-	-	µmho
Peak Output Current	I <sub>OM</sub>	R <sub>L</sub> = 0Ω	350	500	650	µA
		R <sub>L</sub> = 0Ω, T <sub>A</sub> = 0 to +70°C	300	-	-	µA
Peak Output Voltage:	V <sub>+OM</sub>	R <sub>L</sub> = ∞				
			12	13.5	-	V
Negative	V <sub>-OM</sub>	R <sub>L</sub> = ∞	-12	-14.4	-	V
Amplifier Supply Current	I <sub>A</sub>		0.8	1	1.2	mA
Device Dissipation	P <sub>D</sub>		24	30	36	mW
Input Offset Voltage Sensitivity:	ΔV <sub>IO</sub> /ΔV+		-	-	150	µV/V
			-	-	150	µV/V
Common-Mode Rejection Ratio	CMRR		80	110	-	dB
Common-Mode Input-Voltage	V <sub>ICR</sub>		12 to -12	13.6 to -14.6	-	V
Input Resistance	R <sub>I</sub>		10	26	-	kΩ

**NOTE:**

1. Short circuit may be applied to ground or to either supply.

**Specifications CA3080, CA3080A**

**Electrical Specifications** Typical Values Intended Only for Design Guidance,  $T_A = +25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS	CA3080 TYP	UNITS
		$V_+ = 15\text{V}, V_- = -15\text{V}$ $I_{ABC} = 500\mu\text{A}$		
Input Offset Voltage	$V_{IO}$	$I_{ABC} = 5\mu\text{A}$	0.3	mV
Input Offset Voltage Change	$\Delta V_{IO}$	$I_{ABC} = 500\mu\text{A}$ to $I_{ABC} = 5\mu\text{A}$	0.2	mV
Peak Output Current	$I_{OM}$	$I_{ABC} = 5\mu\text{A}$	5	$\mu\text{A}$
Peak Output Voltage:		$I_{ABC} = 5\mu\text{A}$		
Positive	$V_{+OM}$		13.8	V
Negative	$V_{-OM}$		-14.5	V
Magnitude of Leakage Current		$I_{ABC} = 0, V_{TP} = 0$	0.08	nA
		$I_{ABC} = 0, V_{TP} = 36\text{V}$	0.3	nA
Differential Input Current		$I_{ABC} = 0, V_{DIFF} = 4\text{V}$	0.008	nA
Amplifier Bias Voltage	$V_{ABC}$		0.71	V
Slew Rate:	SR			
Maximum (Uncompensated)			75	V/ $\mu\text{s}$
Unity Gain (Compensated)			50	V/ $\mu\text{s}$
Open-Loop Bandwidth	$BW_{OL}$		2	MHz
Input Capacitance	$C_I$	$f = 1\text{ MHz}$	3.6	pF
Output Capacitance	$C_O$	$f = 1\text{ MHz}$	5.6	pF
Output Resistance	$R_O$		15	M $\Omega$
Input-to-Output Capacitance	$C_{I-O}$	$f = 1\text{ MHz}$	0.024	pF
Propagation Delay	$t_{PHL}, t_{PLH}$	$I_{ABC} = 500\mu\text{A}$	45	ns

**Electrical Specifications** For Equipment Design,  $T_A = +25^\circ\text{C}$ , Unless Otherwise Indicated

PARAMETERS	SYMBOL	TEST CONDITIONS	CA3080A LIMITS			UNITS
		$V_+ = 15\text{V}, V_- = -15\text{V}$ $I_{ABC} = 500\mu\text{A}$	MIN	TYP	MAX	
Input Offset Voltage	$V_{IO}$	$I_{ABC} = 5\mu\text{A}$	-	0.3	2	mV
			-	0.4	2	mV
		$T_A = -55$ to $+125^\circ\text{C}$	-	-	5	mV
Input Offset Voltage Change	$\Delta V_{IO}$	$I_{ABC} = 500\mu\text{A}$ to $I_{ABC} = 5\mu\text{A}$	-	0.1	3	mV
Input Offset Current	$I_{IO}$		-	0.12	0.6	$\mu\text{A}$
Input Bias Current	$I_I$		-	2	5	$\mu\text{A}$
		$T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$	-	-	15	$\mu\text{A}$
Forward Transconductance (Large Signal)	$g_M$		7700	9600	12000	$\mu\text{mho}$
		$T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$	4000	-	-	$\mu\text{mho}$
Peak Output Current	$I_{OM}$	$I_{ABC} = 5\mu\text{A}, R_L = 0\Omega$	3	5	7	$\mu\text{A}$
		$R_L = 0\Omega$	350	500	650	$\mu\text{A}$
		$R_L = 0\Omega, T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$	300	-	-	$\mu\text{A}$

Specifications CA3080, CA3080A

Electrical Specifications For Equipment Design,  $T_A = +25^\circ\text{C}$ , Unless Otherwise Indicated (Continued)

PARAMETERS	SYMBOL	TEST CONDITIONS $V_+ = 15\text{V}, V_- = -15\text{V}$ $I_{ABC} = 500\mu\text{A}$	CA3080A LIMITS			UNITS
			MIN	TYP	MAX	
Peak Output Voltage:		$I_{ABC} = 5\mu\text{A}, R_L = \infty$				
Positive	$V_{+OM}$		12	13.8	-	V
Negative	$V_{-OM}$		-12	-14.5	-	V
Positive	$V_{+OM}$	$R_L = \infty$	12	13.5	-	V
Negative	$V_{-OM}$		-12	-14.4	-	V
Amplifier Supply Current	$I_A$		0.8	1	1.2	mA
Device Dissipation	$P_D$		24	30	38	mW
Input Offset Voltage Sensitivity:						
Positive	$\Delta V_{IO}/\Delta V^*$		-	-	150	$\mu\text{V/V}$
Negative	$\Delta V_{IO}/\Delta V^*$		-	-	150	$\mu\text{V/V}$
Magnitude of Leakage Current		$I_{ABC} = 0, V_{TP} = 0$	-	0.08	5	nA
		$I_{ABC} = 0, V_{TP} = 36\text{V}$	-	0.3	5	nA
Differential Input Current		$I_{ABC} = 0, V_{DIFF} = 4\text{V}$	-	0.008	5	nA
Common-Mode Rejection Ratio	CMRR		80	110	-	dB
Common-Mode Input-Voltage Range	$V_{ICR}$		12 to -12	13.6 to -14.6	-	V
Input Resistance	$R_i$		10	26	-	k $\Omega$

Electrical Specifications Typical Values Intended Only for Design Guidance,  $T_A = +25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS $V_+ = 15\text{V}, V_- = -15\text{V}$ $I_{ABC} = 500\mu\text{A}$	CA3080A TYP	UNITS
Slew Rate:				
Maximum (Uncompensated)	SR		75	V/ $\mu\text{s}$
Unity Gain (Compensated)			50	V/ $\mu\text{s}$
Open-Loop Bandwidth	$BW_{OL}$		2	MHz
Input Capacitance	$C_i$	$f = 1\text{ MHz}$	3.6	pF
Output Capacitance	$C_o$	$f = 1\text{ MHz}$	5.6	pF
Output Resistance	$R_o$		15	M $\Omega$
Input-to-Output Capacitance	$C_{iO}$	$f = 1\text{ MHz}$	0.024	pF
Input Offset Voltage Temperature Drift	$\Delta V_{IO}/\Delta T$	$I_{ABC} = 100\mu\text{A}, T_A = -55^\circ\text{C to } +125^\circ\text{C}$	3.0	$\mu\text{V}/^\circ\text{C}$
Propagation Delay	$t_{PHL}, t_{PLH}$	$I_{ABC} = 500\mu\text{A}$	45	ns

4.5 Inspection and Test Records The supplier shall maintain inspection and test records for 36 months after hardware delivery to MIT. Test data for all electrical tests, screening, DPA, and QCI inspections shall be submitted to MIT with the delivery of flight parts.

4.6 Source Inspection

4.6.1 Government Source Inspection (GSI) The government has the right to inspect any or all of the work included in this order at the supplier's plant. In the event that Government Source Inspection (GSI) is imposed, the Government quality representative who has been delegated NASA quality assurance functions for this procurement shall be notified immediately upon receipt of this order. The Government representative shall also be notified 48 hours in advance of the time that parts are ready for inspection or test.

4.6.2 MIT Source Inspection MIT Performance Assurance will impose mandatory inspection points (MIPs) at wire bonding (precap visual examination) and final test, and must be notified 2 weeks before parts are ready for MIT Inspection. (call area code 617, phone 253-7555).

5.0 **PACKAGING**

5.1 Packaging requirements Packaging shall be in accordance with paragraph 5.1 of MIL-M-38510.

6.0 **NOTES**

6.1 Approved Source of Supply

Chip Supply  
7725 N. Orange Blossom Trail  
Orlando, Florida 32810-2696

Cage Code: 57300



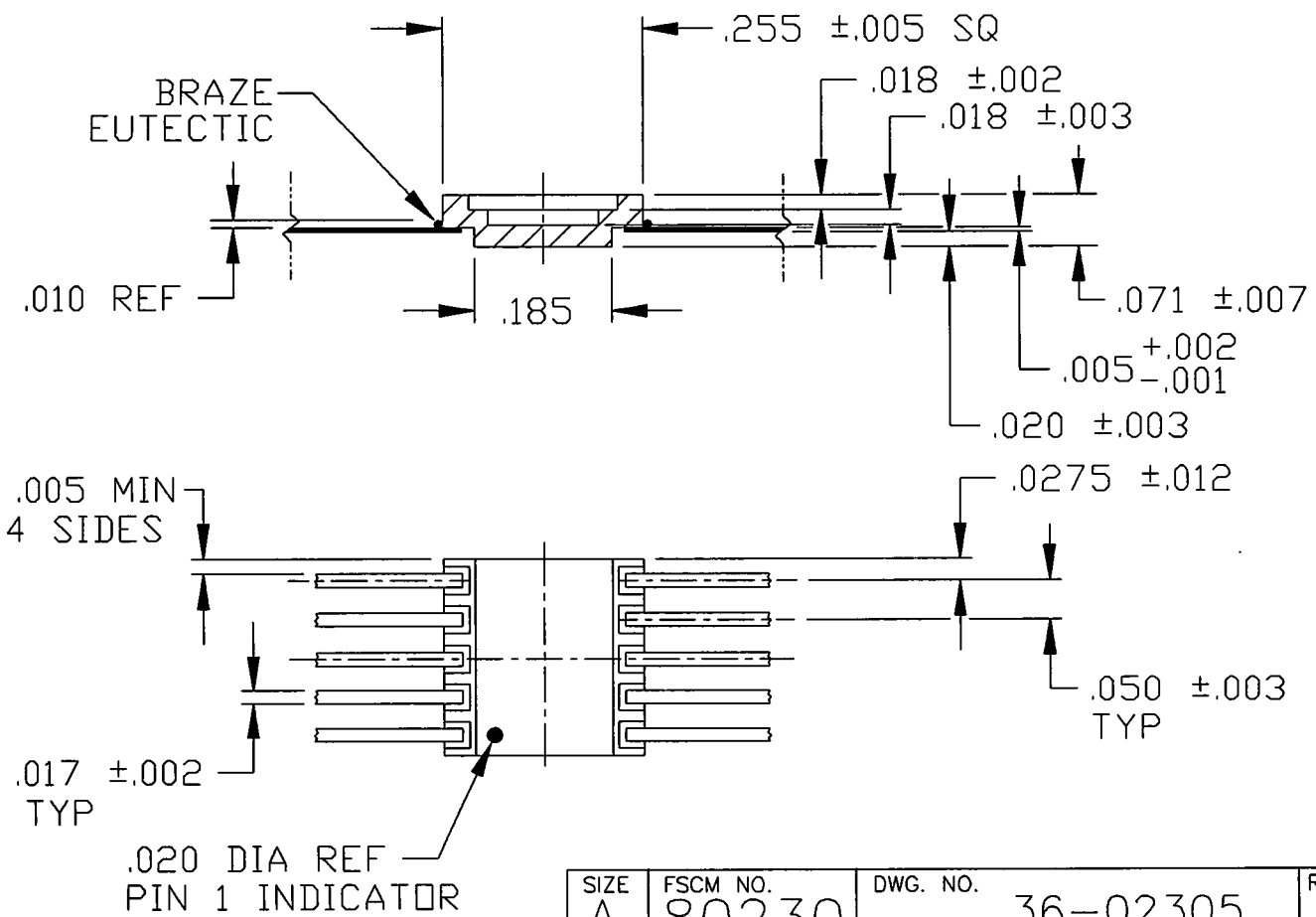
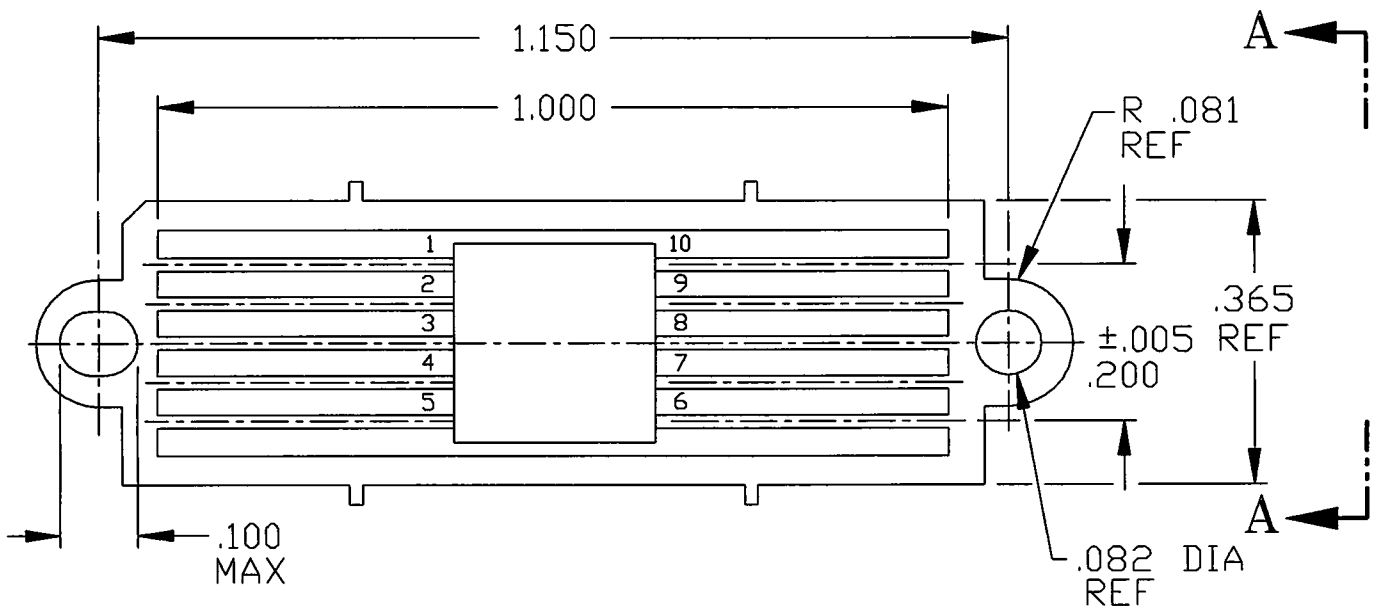
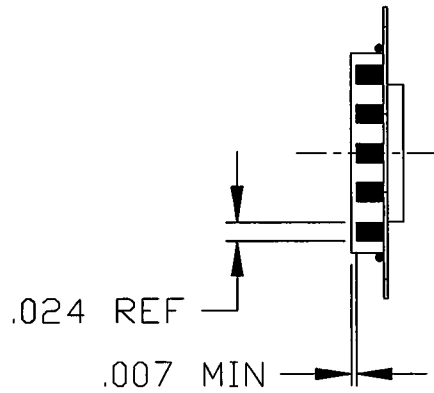


FIGURE I

SIZE A	FSCM NO. 80230	DWG. NO. 36-02305	REV.
SCALE 4:1		SHEET 9	



VIEW A-A

PINOUT INFORMATION		
DIE	PACKAGE	FUNCTION
1	1	NC
2	2	INV INPUT
	3	NC
3	4	NON-INV-INPUT
4	5	V-
5	6	AMPLIFIER BIAS INPUT
6	8	OUTPUT
7	9	V+
	10	NC

TABLE I

SIZE A	FSCM NO. 80230	DWG. NO. 36-02305	REV.
SCALE 4:1		SHEET 10	